

SKM 600GA126D



SEMITRANS™ 4

Trench IGBT Modules

SKM 600GA126D

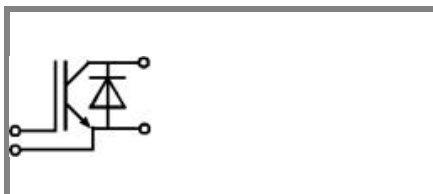
Target Data

Features

- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_C$

Typical Applications

- AC inverter drives
- UPS
- Electronic welders



GA

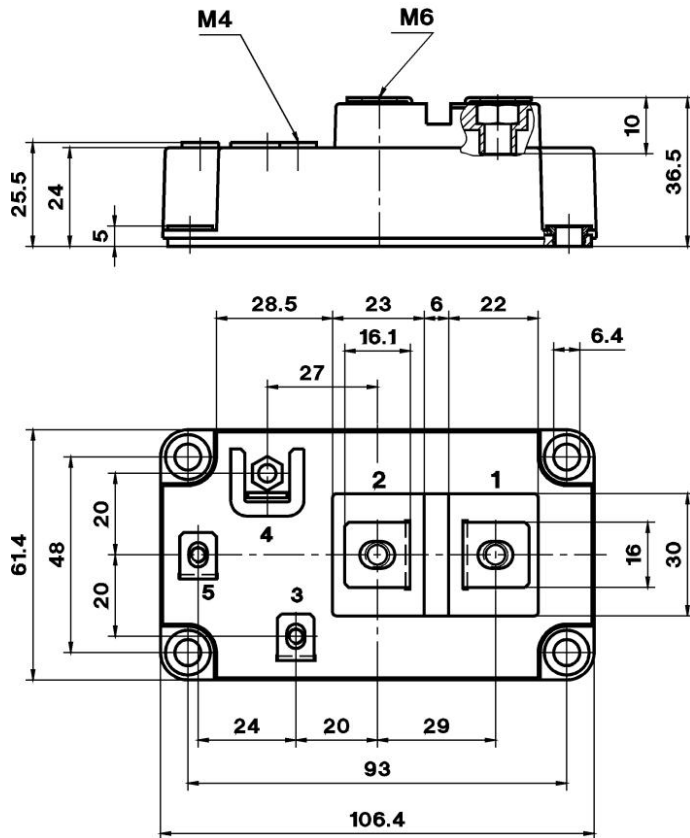
Absolute Maximum Ratings		$T_{case} = 25^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}		1200	V
I_C	$T_c = 25 (80)^\circ\text{C}$	660 (460)	A
I_{CRM}	$t_p = 1 \text{ ms}$	800	A
V_{GES}		± 20	V
T_{vj} (T_{stg})	$T_{OPERATION} \leq T_{stg}$	-40 ... + 150 (125)	$^\circ\text{C}$
V_{isol}	AC, 1 min.	4000	V
Inverse diode			
I_F	$T_c = 25 (80)^\circ\text{C}$	490 (340)	A
I_{FRM}	$t_p = 1 \text{ ms}$	800	A
I_{FSM}	$t_p = 10 \text{ ms}$; sin.; $T_j = 150^\circ\text{C}$	2900	A

Characteristics		$T_{case} = 25^\circ\text{C}$, unless otherwise specified			Units
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}$; $I_C = 16 \text{ mA}$	5	5,8	6,5	V
I_{CES}	$V_{GE} = 0$; $V_{CE} = V_{CES}$; $T_j = 25 (125)^\circ\text{C}$				mA
$V_{CE(TO)}$	$T_j = 25 (125)^\circ\text{C}$		1 (0,9)	1,2 (1,1)	V
r_{CE}	$V_{GE} = 15 \text{ V}$; $T_j = 25 (125)^\circ\text{C}$		1,8 (2,8)	1 (3,4)	$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 400 \text{ A}$; $V_{GE} = 15 \text{ V}$; chip level		1,7 (2)	2,15 (2,45)	V
C_{ies}	under following conditions		29		nF
C_{oes}	$V_{GE} = 0$; $V_{CE} = 25 \text{ V}$; $f = 1 \text{ MHz}$		1,5		nF
C_{res}			1,3		nF
L_{CE}				20	nH
$R_{CC'+EE'}$	res.; terminal-chip $T_c = 25 (125)^\circ\text{C}$		0,35 (0,5)		$\text{m}\Omega$
$t_{d(on)}$	$V_{CC} = 600 \text{ V}$; $I_{Cnom} = 400 \text{ A}$		290		ns
t_r	$R_{Gon} = R_{Goff} = 2 \Omega$; $T_j = 125^\circ\text{C}$		60		ns
$t_{d(off)}$	$V_{GE} \pm 15 \text{ V}$		670		ns
t_f			80		ns
$E_{on} (E_{off})$			39 (64)		mJ
Inverse diode					
$V_F = V_{EC}$	$I_{Fnom} = 400 \text{ A}$; $V_{GE} = 0 \text{ V}$; $T_j = 25 (125)^\circ\text{C}$		1,6 (1,6)	1,8 (1,8)	V
$V_{(TO)}$	$T_j = 25 (125)^\circ\text{C}$		1 (0,8)	1,1 (0,9)	V
r_T	$T_j = 25 (125)^\circ\text{C}$		1,5 (2)	1,8 (2,3)	$\text{m}\Omega$
I_{RRM}	$I_{Fnom} = 400 \text{ A}$; $T_j = 125 ()^\circ\text{C}$		475		A
Q_{rr}	$di/dt = 7600 \text{ A}/\mu\text{s}$		96		μC
E_{rr}	$V_{GE} = 0 \text{ V}$		41		mJ
Thermal characteristics					
$R_{th(j-c)}$	per IGBT			0,055	K/W
$R_{th(j-c)D}$	per Inverse Diode			0,125	K/W
$R_{th(c-s)}$	per module			0,038	K/W
Mechanical data					
M_s	to heatsink				Nm
M_t	to terminals				Nm
w					g

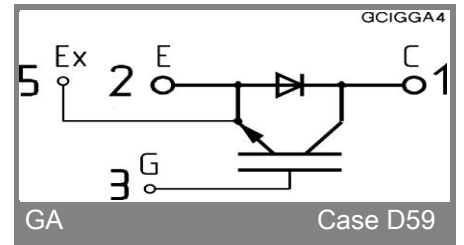
UL Recognized
File no. E 63 532

Dimensions in mm

CASED59



Case D 59



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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